

# K Vedam

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3195075/publications.pdf>

Version: 2024-02-01

154  
papers

4,308  
citations

94415

37  
h-index

144002

57  
g-index

163  
all docs

163  
docs citations

163  
times ranked

1771  
citing authors

#	ARTICLE	IF	CITATIONS
1	Dielectric and Thermal Study of $(\text{NH}_4)_2\text{SO}_4$ and $(\text{NH}_4)_2\text{BeF}_4$ Transitions. Physical Review, 1958, 112, 405-412.	2.7	193
2	Spectroscopic ellipsometry: a historical overview. Thin Solid Films, 1998, 313-314, 1-9.	1.8	145
3	Nondestructive depth profiling by spectroscopic ellipsometry. Applied Physics Letters, 1985, 47, 339-341.	3.3	135
4	Thin film deposition by a new laser ablation and plasma hybrid technique. Applied Physics Letters, 1989, 54, 2455-2457.	3.3	121
5	Ammonium Hydrogen Sulfate: A New Ferroelectric with Low Coercive Field. Physical Review, 1958, 111, 1508-1510.	2.7	117
6	Spectroscopic ellipsometry: A new tool for nondestructive depth profiling and characterization of interfaces. Journal of Applied Physics, 1986, 59, 694-701.	2.5	113
7	Ferroelectricity in Di-Glycine Nitrate $(\text{NH}_2\text{CH}_2\text{COOH})_2 \cdot \text{HNO}_3$ . Physical Review, 1958, 111, 430-432.	2.7	94
8	Ferroelectric Transition in Rubidium Bisulfate. Physical Review, 1960, 117, 1502-1503.	2.7	89
9	Variation of Refractive Index of MgO with Pressure to 7 kbar. Physical Review, 1966, 146, 548-554.	2.7	88
10	Optical Anisotropy of Silicon Single Crystals. Physical Review B, 1971, 3, 2567-2571.	3.2	87
11	Investigation of the void structure in amorphous germanium thin films as a function of low energy ion bombardment. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1631-1635.	2.1	86
12	$\text{LiH}_3(\text{SeO}_3)_2$ : New Room-Temperature Ferroelectric. Physical Review, 1959, 114, 1217-1218.	2.7	85
13	Room-Temperature Ferroelectricity in Lithium Hydrazinium Sulfate, $\text{Li}(\text{N}_2\text{H}_5)\text{SO}_4$ . Physical Review, 1958, 111, 1467-1468.	2.7	78
14	Direct Optical Observation of the Semiconductor-to-Metal Transition in SmS under Pressure. Physical Review B, 1972, 6, 3023-3026.	3.2	78
15	Fast scanning spectroelectrochemical ellipsometry: In-situ characterization of gold oxide. Surface Science, 1990, 233, 341-350.	1.9	74
16	Variation of the refractive indices of $\text{CaF}_2$ , $\text{BaF}_2$ and $\text{PbF}_2$ with pressure to 7 kb. Journal of Physics and Chemistry of Solids, 1966, 27, 1563-1566.	4.0	71
17	Piezoelectric and elastooptic properties of liquids under high pressure. II. Refractive index vs density. Journal of Chemical Physics, 1978, 69, 4772-4778.	3.0	71
18	Piezoelectric and elastooptic properties of liquids under high pressure. I. Refractive index vs pressure and strain. Journal of Chemical Physics, 1978, 69, 4762-4771.	3.0	69

#	ARTICLE	IF	CITATIONS
19	Real Time Spectroscopic Ellipsometry: In Situ Characterization of Pyrrole Electropolymerization. Journal of the Electrochemical Society, 1991, 138, 3266-3275.	2.9	63
20	Pressure Dependence of the Refractive Indices of the Hexagonal Crystals Beryl, $\hat{\Gamma}$ -CdS, $\hat{\Gamma}$ -ZnS, and ZnO. Physical Review, 1969, 181, 1196-1201.	2.7	60
21	Characterization of real surfaces by ellipsometry. Surface Science, 1972, 29, 379-395.	1.9	57
22	Elastic Constants of Selenium in the Hexagonal and Glassy Phases. Journal of Applied Physics, 1966, 37, 3432-3434.	2.5	51
23	Nonlinear Variation of Refractive Index of Vitreous Silica with Pressure to 7 Kbars. Journal of the American Ceramic Society, 1966, 49, 531-535.	3.8	51
24	Ellipsometric Method for the Determination of All the Optical Parameters of the System of an Isotropic Nonabsorbing Film on an Isotropic Absorbing Substrate Optical Constants of Silicon*. Journal of the Optical Society of America, 1969, 59, 64.	1.2	51
25	Pressure Dependence of the Refractive Indices of the Tetragonal Crystals: ADP, KDP, CaMoO <sub>4</sub> , CaWO <sub>4</sub> , and Rutile*. Journal of the Optical Society of America, 1968, 58, 1446.	1.2	50
26	Raman spectrum of strontium titanate. European Physical Journal A, 1961, 163, 158-164.	2.5	48
27	Generalized Ellipsometric Method for the Absorbing Substrate Covered with a Transparent-Film System Optical Constants of Silicon at 3655 Å...*. Journal of the Optical Society of America, 1972, 62, 16.	1.2	47
28	Spectroscopic ellipsometry studies on ion beam sputter deposited Pb(Zr, Ti)O <sub>3</sub> films on sapphire and Pt-coated silicon substrates. Thin Solid Films, 1993, 230, 15-27.	1.8	47
29	Effect of preparation conditions on the morphology and electrochromic properties of amorphous tungsten oxide films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1881-1887.	2.1	47
30	New Room-Temperature Ferroelectric. Physical Review, 1958, 110, 1309-1311.	2.7	46
31	Analytic solution of the pseudo-Brewster angle. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 1986, 3, 1772.	1.5	43
32	Nonlinear Variation of the Refractive Indices of $\hat{\Gamma}$ -Quartz with Pressure*. Journal of the Optical Society of America, 1967, 57, 1140.	1.2	42
33	Density of amorphous germanium films by spectroscopic ellipsometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1986, 4, 577-582.	2.1	41
34	Thickness dependence of optical gap and void fraction for sputtered amorphous germanium. Physical Review B, 1987, 35, 9368-9371.	3.2	41
35	Optical characterization of a four-medium thin film structure by real time spectroscopic ellipsometry: amorphous carbon on tantalum. Applied Optics, 1991, 30, 2692.	2.1	41
36	Non-isomorphism of ferroelectric phases of ammonium sulfate and ammonium fluoberyllate. Acta Crystallographica, 1958, 11, 307-307.	0.5	40

#	ARTICLE	IF	CITATIONS
37	Crystal Structure of Ferroelectric $\text{LiH}_3(\text{SeO}_3)_2$ . <i>Physical Review</i> , 1960, 119, 1252-1255.	2.7	39
38	Electroreflectance in GeSi alloys under hydrostatic pressure. <i>Solid State Communications</i> , 1971, 9, 1187-1191.	1.9	39
39	Roughness measurements by spectroscopic ellipsometry. <i>Applied Optics</i> , 1985, 24, 3773.	2.1	39
40	Simultaneous determination of dispersion relation and depth profile of thorium fluoride thin film by spectroscopic ellipsometry. <i>Thin Solid Films</i> , 1988, 166, 325-334.	1.8	38
41	Proper choice of the error function in modeling spectroellipsometric data. <i>Applied Optics</i> , 1986, 25, 2013.	2.1	37
42	Formation and nondestructive characterization of ion implanted silicon-oxide-insulator layers. <i>Applied Physics Letters</i> , 1987, 51, 343-345.	3.3	35
43	Ion-implantation induced anomalous surface amorphization in silicon. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 1994, 85, 335-339.	1.4	34
44	The Laser as a Light Source for Ultramicroscopy and Light Scattering by Imperfections in Crystals. Investigation of Imperfections in LiF, MgO, and Ruby. <i>Journal of Applied Physics</i> , 1966, 37, 2551-2557.	2.5	33
45	Simultaneous determination of refractive index, its dispersion and depth-profile of magnesium oxide thin film by spectroscopic ellipsometry. <i>Applied Optics</i> , 1989, 28, 2691.	2.1	33
46	Simultaneous and Independent Determination of the Refractive Index and the Thickness of Thin Films by Ellipsometry*. <i>Journal of the Optical Society of America</i> , 1968, 58, 526.	1.2	30
47	Variation of the refractive indices of KBr and KI with pressure to 14 kbars. <i>Materials Research Bulletin</i> , 1969, 4, 573-579.	5.2	30
48	Real-time and spectroscopic ellipsometry characterization of diamond and diamond-like carbon. <i>Thin Solid Films</i> , 1989, 181, 565-578.	1.8	30
49	Spectroscopic ellipsometry studies of crystalline silicon implanted with carbon ions. <i>Journal of Applied Physics</i> , 1990, 67, 3555-3559.	2.5	30
50	The Elastic and Photoelastic Constants of Fused Quartz. <i>Physical Review</i> , 1950, 78, 472-473.	2.7	29
51	Real time spectroscopic ellipsometry characterization of the nucleation of diamond by filament-assisted chemical vapor deposition. <i>Journal of Applied Physics</i> , 1992, 71, 5287-5289.	2.5	29
52	Determination of the optical constants of an inhomogeneous transparent $\text{LaF}_3$ thin film on a transparent substrate by spectroscopic ellipsometry. <i>Optics Letters</i> , 1992, 17, 538.	3.3	29
53	Characterization of inhomogeneous transparent thin films on transparent substrates by spectroscopic ellipsometry: refractive indices $n(\lambda)$ of some fluoride coating materials. <i>Applied Optics</i> , 1994, 33, 2664.	2.1	29
54	Photoelastic Properties of Sapphire ( $\text{Al}_2\text{O}_3$ ). <i>Journal of Applied Physics</i> , 1967, 38, 4555-4556.	2.5	26

#	ARTICLE	IF	CITATIONS
55	Generalized ellipsometric method for the determination of all the optical constants of the system: Optically absorbing film on an absorbing substrate. <i>Surface Science</i> , 1976, 56, 49-63.	1.9	26
56	Thickness-dependent void fraction of rf-sputtered amorphous Ge films by spectroscopic ellipsometry. <i>Applied Physics Letters</i> , 1986, 49, 328-330.	3.3	26
57	Nondestructive depth profiling of ZnS and MgO films by spectroscopic ellipsometry. <i>Optics Letters</i> , 1987, 12, 456.	3.3	26
58	Determination of the optical function $n(\hat{\lambda})$ of vitreous silica by spectroscopic ellipsometry with an achromatic compensator. <i>Applied Optics</i> , 1993, 32, 6391.	2.1	26
59	Piezo- and elasto-optic properties of liquids under high pressure. III. Results on twelve more liquids. <i>Journal of Chemical Physics</i> , 1980, 73, 4577-4584.	3.0	25
60	Epitaxial Growth of Ice Crystals on the Muscovite Cleavage Plane and Their Relation to Partial Dislocations. <i>Journal of Applied Physics</i> , 1971, 42, 516-520.	2.5	23
61	Explosive crystallization of rf-sputtered amorphous CdTe films. <i>Journal of Electronic Materials</i> , 1981, 10, 433-443.	2.2	23
62	Pressure dependence of the refractive index and dielectric constant in a fluoroperovskite, $\text{KMgF}_3$ . <i>Physical Review B</i> , 1984, 29, 6921-6925.	3.2	23
63	Characterization of defects in real surfaces by ellipsometry. <i>Surface Science</i> , 1976, 56, 221-236.	1.9	22
64	Electrical characteristics of r.f.-sputtered CdTe thin-films for photovoltaic applications. <i>Solid-State Electronics</i> , 1984, 27, 329-337.	1.4	22
65	Ar ion beam and $\text{CCl}_4$ reactive ion etching: A comparison of etching damage and of damage passivation by hydrogen. <i>Journal of Applied Physics</i> , 1985, 58, 4282-4291.	2.5	22
66	Spectroscopic ellipsometry study of glow-discharge-deposited thin films of $\text{a-Ge:H}$ . <i>Journal of Applied Physics</i> , 1986, 60, 3724-3731.	2.5	22
67	Nonlinear Piezo-Optic Behavior of Sphalerite ( $\hat{\lambda}$ -ZnS). <i>Physical Review</i> , 1966, 150, 766-767.	2.7	21
68	Optical interferometry in liquids at high pressures to 14 kilobars. <i>Review of Scientific Instruments</i> , 1977, 48, 245-246.	1.3	21
69	Refractive index of liquids at high pressures. <i>Critical Reviews in Solid State and Materials Sciences</i> , 1983, 11, 1-45.	12.3	21
70	Characterization of ion beam-induced surface modification of diamond films by real time spectroscopic ellipsometry. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1991, 9, 1123-1128.	2.1	21
71	Characterization of real surfaces of vitreous silica by ellipsometry. <i>Materials Research Bulletin</i> , 1974, 9, 1503-1509.	5.2	20
72	Piezo-optic Behavior of Water and Carbon Tetrachloride under High Pressure. <i>Physical Review Letters</i> , 1975, 35, 1014-1016.	7.8	20

#	ARTICLE	IF	CITATIONS
73	Retroreflection from spherical glass beads in highway pavement markings 2: Diffuse reflection (a first) Tj ETQq1 1 0,784314 rgBT /Overl	2.1	20
74	Optical Characterization of Inhomogeneous Transparent Films on Transparent Substrates by Spectroscopic Ellipsometry. Physics of Thin Films, 1994, , 191-247.	1.1	20
75	Non-linear piezo-optics. Acta Crystallographica, 1967, 22, 630-634.	0.5	19
76	Importance of using Eulerian representation of strain in high pressure studies on liquids. Journal of Chemical Physics, 1982, 77, 1461-1463.	3.0	19
77	Monitoring ion etching of GaAs/AlGaAs heterostructures by real time spectroscopic ellipsometry: Determination of layer thicknesses, compositions, and surface temperature. Applied Physics Letters, 1992, 60, 2776-2778.	3.3	19
78	Piezo- and thermo-optic behavior of spinel (MgAl <sub>2</sub> O <sub>4</sub> ). Journal of Solid State Chemistry, 1975, 12, 213-218.	2.9	18
79	Retroreflection from spherical glass beads in highway pavement markings 1: Specular reflection. Applied Optics, 1978, 17, 1855.	2.1	18
80	Processing speckle photography data: circular imaging aperture. Applied Optics, 1983, 22, 653.	2.1	18
81	Characterization of the interface between Ge+ implanted crystalline silicon and its thermally grown oxide by spectroscopic ellipsometry. Journal of Applied Physics, 1990, 67, 599-603.	2.5	18
82	Ion beam etching of GaAs and GaAs/AlGaAs heterostructures probed in real time by spectroscopic ellipsometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 810-815.	2.1	18
83	Speckle photography of lateral sinusoidal vibrations: error due to varying halo intensity. Applied Optics, 1981, 20, 3388.	2.1	17
84	Studies on inhomogeneous transparent optical coatings on transparent substrates by spectroscopic ellipsometry. Thin Solid Films, 1993, 234, 439-442.	1.8	17
85	Piezo-Optic Properties of Amorphous Selenium at a Wavelength of 115 $\frac{1}{4}$ . Journal of the Optical Society of America, 1970, 60, 800.	1.2	16
86	High-dose carbon ion implantation studies in silicon. Thin Solid Films, 1988, 163, 323-329.	1.8	16
87	Examination of Imperfect Muscovite Crystals by X-Ray Diffraction Methods. Journal of Applied Physics, 1970, 41, 50-53.	2.5	15
88	Real-time spectroscopic ellipsometry study of the electrochemical deposition of polypyrrole thin films. Thin Solid Films, 1990, 193-194, 350-360.	1.8	15
89	Elastic and photoelastic properties of some optical glasses. Proceedings of the Indian Academy of Sciences - Section A, 1950, 31, 450-458.	0.2	14
90	Piezo-optic behaviour of rubidium chloride up to the phase transition point. Journal of Materials Science, 1966, 1, 310-312.	3.7	14

#	ARTICLE	IF	CITATIONS
91	Piezo-optic behavior of forsterite, Mg <sub>2</sub> SiO <sub>4</sub> . Journal of Physics and Chemistry of Solids, 1972, 33, 1251-1255.	4.0	14
92	Ellipsometric studies of environment-sensitive polish layers of glass. Journal of Applied Physics, 1977, 48, 1155-1157.	2.5	14
93	Selective counting path of Young's fringes in speckle photography for eliminating diffraction halo effects. Applied Optics, 1983, 22, 2242.	2.1	14
94	Finite size effects on lattice vibrations of ionic crystals and measurements of infrared absorption spectra. Physica Status Solidi A, 1970, 3, 647-656.	1.7	13
95	Variation of the refractive index of boric oxide glasses with hydrostatic pressure to 7 kbar. Journal of Applied Physics, 1972, 43, 3623-3627.	2.5	13
96	Optical Constants of Silicon at 5461 Å...*. Journal of the Optical Society of America, 1972, 62, 596.	1.2	12
97	PIEZO-AND THERMO-OPTIC BEHAVIOR OF LiNbO <sub>3</sub> . Applied Physics Letters, 1968, 12, 138-140.	3.3	11
98	Piezo-and thermo-optic behavior of LiTaO <sub>3</sub> . Journal of Applied Physics, 1981, 52, 944-947.	2.5	11
99	Real time monitoring of filament-assisted chemically vapor deposited diamond by spectroscopic ellipsometry. Surface and Coatings Technology, 1991, 49, 381-386.	4.8	11
100	Variation of the refractive indices of calcite, with pressure to 7 kbar. Physica Status Solidi (B): Basic Research, 1968, 26, 285-290.	1.5	10
101	The study of dislocations in muscovite mica by X-ray transmission topography. Philosophical Magazine and Journal, 1970, 22, 255-268.	1.7	10
102	Nondestructive Depth-Profiling of Multilayer Structures by Spectroscopic Ellipsometry. MRS Bulletin, 1987, 12, 21-23.	3.5	10
103	Characterisation of thin surface films on germanium in various solvents by ellipsometry. Journal of Materials Science, 1971, 6, 969-973.	3.7	9
104	Intrinsic Stress in a-Germanium Films Deposited by RF-Magnetron Sputtering. Materials Research Society Symposia Proceedings, 1988, 130, 355.	0.1	9
105	Ion-implantation-caused special damage profiles determined by spectroscopic ellipsometry in crystalline and in relaxed (annealed) amorphous silicon. Thin Solid Films, 1993, 233, 117-121.	1.8	9
106	Hydrogen diffusion and reaction processes in thin films investigated by real time spectroscopic ellipsometry. Thin Solid Films, 1993, 233, 276-280.	1.8	9
107	THIN FILM CHARACTERIZATION BY ELECTRON MICROPROBE AND ELLIPSOMETRY: SiO <sub>2</sub> FILMS ON SILICON. Applied Physics Letters, 1969, 14, 43-45.	3.3	8
108	A critical evaluation of equations of state by piezo-optic measurements. Journal of Applied Physics, 1979, 50, 1328-1333.	2.5	8

#	ARTICLE	IF	CITATIONS
109	Measurement of subspeckle-size changes by laser-speckle photography. Optics Letters, 1979, 4, 406.	3.3	8
110	Comparative study of the effect of annealing of nitrogen-implanted silicon-on-insulator structures by spectroscopic ellipsometry, cross-sectional transmission electron microscopy and Rutherford backscattering spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 12, 177-184.	3.5	8
111	Photoelastic properties of barite. Proceedings of the Indian Academy of Sciences - Section A, 1951, 34, 161.	0.2	7
112	Spectroscopic Ellipsometry Study of rf-Sputtered a-Ge Films. Materials Research Society Symposia Proceedings, 1984, 38, 301.	0.1	7
113	Nonuniformity in void concentration between the initial and final growth stage of sputtered a-Ge films studied using spectroscopic ellipsometry. Physical Review B, 1987, 36, 6206-6208.	3.2	7
114	Photoelastic constants of sodium chlorate from ultrasonic diffraction. Proceedings of the Indian Academy of Sciences - Section A, 1951, 34, 240.	0.2	6
115	Optical constants of germanium by ellipsometry. Physics Letters, Section A: General, Atomic and Solid State Physics, 1969, 29, 428-429.	2.1	6
116	Nonlinear variation of the induced birefringence of vitreous silica with uniaxial stress to 7 kbar. Journal of Applied Physics, 1972, 43, 3724-3728.	2.5	6
117	Stress-optic coefficient of ZnSe at 106 $\frac{1}{4}$ $\mu$ m. Applied Optics, 1981, 20, 2878.	2.1	6
118	Growth of color centres and hardening of CaF <sub>2</sub> by heavy dose of $\hat{\nu}^3$ -irradiation. Physica Status Solidi A, 1973, 19, 625-634.	1.7	5
119	Variation of refractive index of polystyrene with pressure to 7 kbar. Journal of Applied Physics, 1976, 47, 2443-2446.	2.5	5
120	Direct observation of laser speckles for real-time analysis of lateral motions. Optics Letters, 1981, 6, 511.	3.3	5
121	Real-time spectroscopic ellipsometry for determination of the optical functions of ion-beam-deposited hydrogenated amorphous carbon. Thin Solid Films, 1990, 193-194, 361-370.	1.8	5
122	Dispersion of the Elasto-Optic Constants of Potassium Halides. , 1975, , 169-177.		5
123	Hardening of CaF <sub>2</sub> single-crystal surfaces due to contamination by atmospheric oxygen. Journal of Applied Physics, 1972, 43, 4396-4400.	2.5	4
124	Complete 3-D deformation analysis in the white light speckle method. Applied Optics, 1983, 22, 213.	2.1	4
125	Electrical, Optical and Structural Properties of Thin SiO <sub>2</sub> Films On Si. Materials Research Society Symposia Proceedings, 1987, 105, 169.	0.1	4
126	Spectroscopic ellipsometry of amorphous Ni <sub>0.95</sub> Tb <sub>0.05</sub> and crystalline nickel. Materials Science and Engineering, 1988, 99, 281-283.	0.1	4



#	ARTICLE	IF	CITATIONS
127	Morphology Control Of The Electrochromic Effect In Tungsten Oxide Thin Films. Materials Research Society Symposia Proceedings, 1991, 255, 275.	0.1	4
128	Unusual white light conoscopic figure in single crystal lithium metagermanate Li <sub>2</sub> GeO <sub>3</sub> . Applied Optics, 1978, 17, 3339_1.	2.1	3
129	Characterization of surfaces of laser-annealed samples by ellipsometry. Surface Science, 1980, 96, 319-328.	1.9	3
130	Laser speckle photography for supersensitive dial gauge. Optics Letters, 1980, 5, 441.	3.3	3
131	The Study of Damage Profile of Ion Implanted Layer on Si by Spectroscopic Ellipsometry. Materials Research Society Symposia Proceedings, 1982, 14, 529.	0.1	3
132	Characterization of Ion Implanted Silicon by Spectroscopic Ellipsometry and Cross Section Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1983, 27, 299.	0.1	3
133	Spectroscopic ellipsometry of sputtered amorphous Ni <sub>0.95</sub> Tb <sub>0.05</sub> and crystalline Ni. Physical Review B, 1988, 38, 1562-1565.	3.2	3
134	Temperature dependence of optical constants of MoS <sub>2</sub> for pyrooptical devices. Applied Optics, 1991, 30, 1583.	2.1	3
135	Application of fringe shifting technique in speckle photography. Pramana - Journal of Physics, 1979, 12, 341-346.	1.8	2
136	Testing the trueness of circular surfaces by laser speckle photography. Applied Optics, 1979, 18, 2351.	2.1	2
137	OPTICAL STUDIES ON THE HIGH PRESSURE PHASE TRANSFORMATIONS IN SILVER IODIDE SINGLE CRYSTALS. , 1973, , 91-99.		2
138	Characterization of Ferroelectric Films by Spectroscopic Ellipsometry. Physics of Thin Films, 1994, , 249-278.	1.1	2
139	Nonlinear Piezo-Optic Behavior of Sphalerite (ZnS). Physical Review, 1969, 177, 1394-1394.	2.7	1
140	Testing the trueness of circular surfaces: a simple holographic method. Applied Optics, 1979, 18, 627.	2.1	1
141	Ordinary paper for position determination of intense laser pulse. Applied Optics, 1979, 18, 4063.	2.1	1
142	Piezo- and elasto-optic properties of deuterium oxide under high pressure. Journal of Chemical Physics, 1980, 72, 1410-1411.	3.0	1
143	Surface Roughness Characterization of Al Films by Spectroscopic Ellipsometry. Materials Research Society Symposia Proceedings, 1985, 54, 669.	0.1	1
144	Supersensitive Dial-Gage Measurement by Observing Rotation of Laser Speckles. Experimental Techniques, 1985, 9, 16-17.	1.5	1

#	ARTICLE	IF	CITATIONS
145	High Dose Carbon Ion Implantation Studies in Silicon. Materials Research Society Symposia Proceedings, 1987, 107, 483.	0.1	1
146	Processing & Characterization Of Thin Films Of SiO <sub>2</sub> On Si For Integrated Circuits. , 1988, 0945, 84.		1
147	Support for rebuttals. Physics Today, 1976, 29, 43-43.	0.3	0
148	Increasing effective size of holography tables. Applied Optics, 1979, 18, 418_1.	2.1	0
149	Formation And Nondestructive Characterization Of Ion Implanted Soi Layers. Proceedings of SPIE, 1987, 0797, 77.	0.8	0
150	SIMULTANEOUS DETERMINATION OF DISPERSION RELATION AND DEPTH PROFILE OF THORIUM FLUORIDE THIN FILM BY SPECTROSCOPIC ELLIPSOMETRY. , 1988, , 325-334.		0
151	5.2.2.5 Trigonal system: Classes 3m (C <sub>3v</sub> ), 32 (D <sub>3d</sub> ), (-3)m (D <sub>3d</sub> ). , 0, , 59-62.		0
152	The Pressure Dependence of the Magnetic Susceptibility of Rare-Earth Substituted Samarium Sulfide. , 1978, , 187-204.		0
153	Piezo-Optic Behavior and the Equation of State of Liquids. , 1979, , 421-427.		0
154	Real time monitoring of filament-assisted chemically vapor deposited diamond by spectroscopic ellipsometry. , 1991, , 381-386.		0